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				Application Number	09/651,998
				Filing Date	August 31, 2000
				First Named Inventor	Lingyi A. Zheng
				Art Unit	2812
				Examiner Name	H. Tsai
				Attorney Docket Number	M4065.0315/P315
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	CA	Okada et al., "Oxynitride gate dielectrics prepared by rapid thermal processing using mixtures of nitrous oxide and oxygen," Applied Phys. Lett., 61 (26), 28 December 1992., America Institute of Physics, pp. 3163-3165.	<input checked="" type="checkbox"/>
	CB	G. Lucovsky, "Ultrathin nitrided gate dielectrics: Plasma processing, chemical characterization, performance, and reliability", IBM Res. Develop., Vol. 43, No. 3. May 1999, pp. 301-326.	<input checked="" type="checkbox"/>

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